

**WHAT IS CLAIMED IS:**

1. A semiconductor integrated circuit device comprising:  
unit areas placed in plural form in a first direction;  
a first line extending in the first direction over said plurality of unit areas;  
a second line extending in the first direction along said plurality of unit areas  
and outside said plurality of unit areas; and  
wiring areas provided adjacent to a first unit area of said plurality of unit areas  
and provided with a third line extending in a second direction, intersecting the first  
direction,  
wherein said first unit area has a MOSFET formed therein,  
wherein said third line is used to connect said second line to a terminal of said  
MOSFET, and  
wherein said third line is separated from said first line electrically.
2. A semiconductor integrated circuit device comprising:  
unit areas placed in plural form in a first direction;  
a first line, formed with a first layer, extending in the first direction over said  
plurality of unit areas;  
a second line extending in the first direction along said plurality of unit areas  
and outside said plurality of unit areas; and  
wiring areas provided adjacent to a first unit area of said plurality of unit areas  
and provided with a third line;

wherein said first unit area has a circuit formed therein,  
wherein said third line connects said second line and a terminal of said circuit,  
wherein said third line is formed with a second layer which is different from  
said first layer, and  
wherein said third line is separated from said first line electrically.

3. A semiconductor integrated circuit device according to claim 2,  
wherein said second layer is formed by a single layer.

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